



STS8050

NPN Silicon Transistor

Descriptions

- High current application
- Radio in class B push-pull operation

Feature

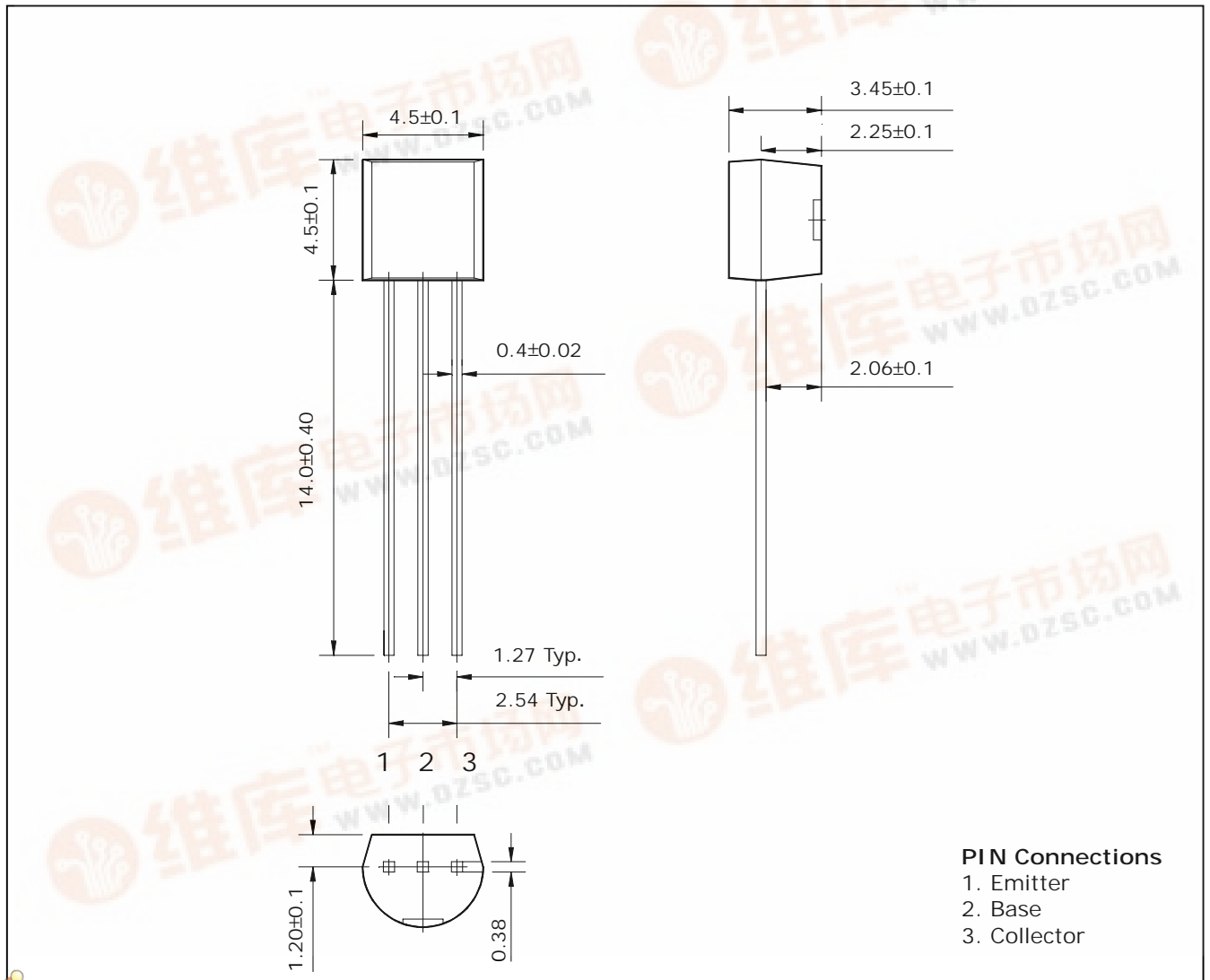
- Complementary pair with STS8550

Ordering Information

Type NO.	Marking	Package Code
STS8050	STS8050	TO-92

Outline Dimensions

unit : mm



PIN Connections

1. Emitter
2. Base
3. Collector



Absolute maximum ratings

(Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Collector-Base voltage	V_{CBO}	30	V
Collector-Emitter voltage	V_{CEO}	25	V
Emitter-Base voltage	V_{EBO}	6	V
Collector current	I_C	800	mA
Emitter current	I_E	-800	mA
Collector dissipation	P_C	625	mW
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55 ~ 150	°C

Electrical Characteristics

(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base breakdown voltage	BV_{CBO}	$I_C=500\mu A, I_E=0$	30	-	-	V
Collector-Emitter breakdown voltage	BV_{CEO}	$I_C=1mA, I_B=0$	25	-	-	V
Collector cut-off current	I_{CBO}	$V_{CB}=15V, I_E=0$	-	-	50	nA
DC current gain	h_{FE}^*	$V_{CE}=1V, I_C=50mA$	85	-	300	-
Collector-Emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$	-	-	0.5	V
Base-Emitter voltage	V_{BE}	$V_{CE}=1V, I_C=500mA$	-	-	1.2	V
Transition frequency	f_T	$V_{CE}=5V, I_C=10mA$	-	120	-	MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	19	-	pF

* : h_{FE} Rank / B : 85~160, C : 120~200, D : 160~300

Electrical Characteristic Curves

Fig. 1 $P_c - T_a$

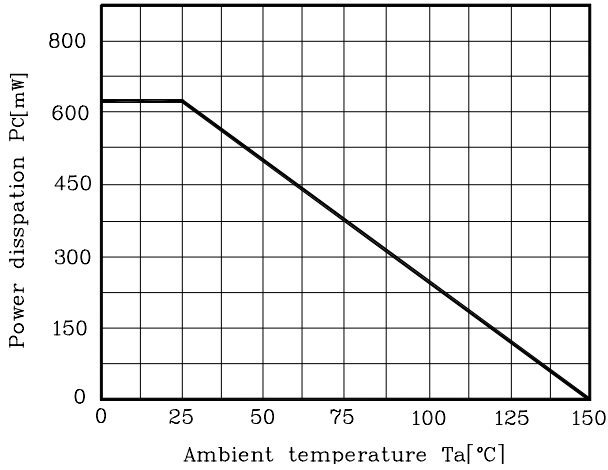


Fig. 2 $I_c - V_{BE}$

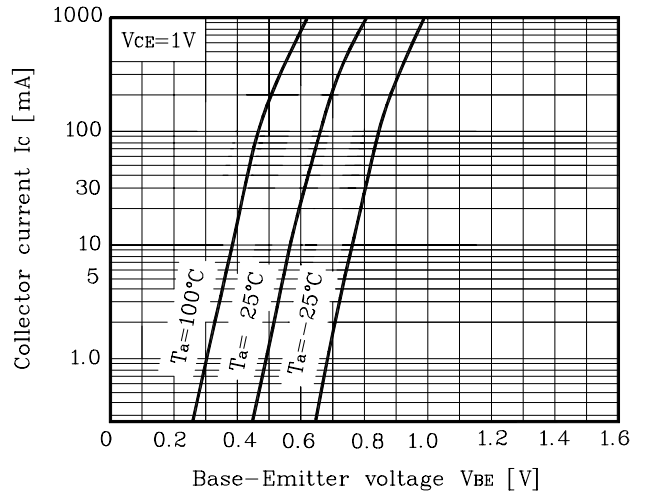


Fig. 3 $I_c - V_{CE}$

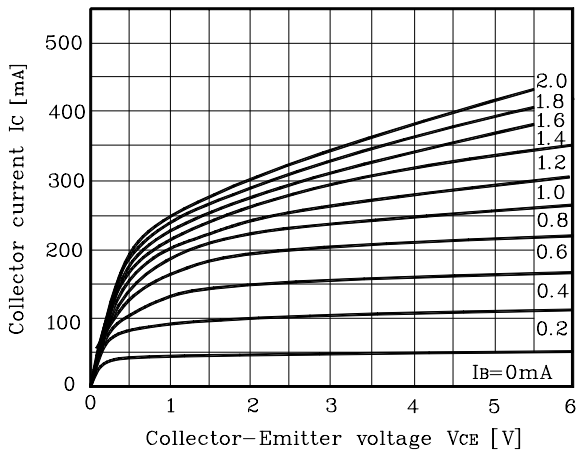


Fig. 4 $V_{CE(SAT)} - I_c$

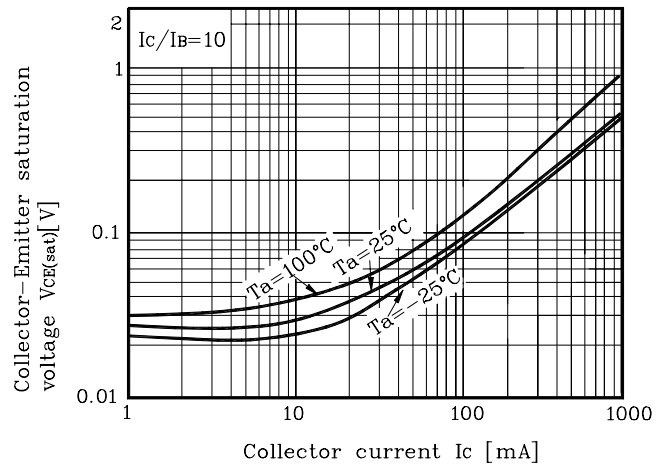


Fig. 5 $h_{FE} - I_c$

